# **Amplifier Transistors**

## **NPN Silicon**

### Features

• Pb–Free Packages are Available\*

#### MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Collector – Emitter Voltage	2N5088 2N5089	V <sub>CEO</sub>	30 25	Vdc
Collector – Base Voltage	2N5088 2N5089	V <sub>CBO</sub>	35 30	Vdc
Emitter – Base Voltage		$V_{\text{EBO}}$	3.0	Vdc
Collector Current – Continuous		Ι <sub>C</sub>	50	mAdc
Total Device Dissipation @ $T_A =$ Derate above 25°C	25°C	PD	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C =$ Derate above 25°C	25°C	PD	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

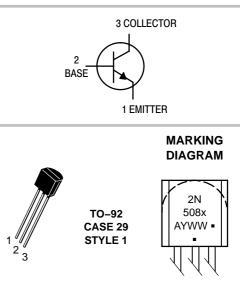
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1.  $R_{\theta,JA}$  is measured with the device soldered into a typical printed circuit board.



## **ON Semiconductor®**

http://onsemi.com



2N508x	=	Device Code
		x = 8 or 9
А	=	Assembly Location
Y	=	Year
WW	=	Work Week
-	=	Pb–Free Package
(Note: Microc	lot	may be in either location)

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>		
2N5088	TO-92	5000 Units/Box		
2N5088G	TO–92 (Pb–Free)	5000 Units/Box		
2N5088RLRA	TO-92	2000/Tape & Reel		
2N5088RLRAG	TO–92 (Pb–Free)	2000/Tape & Reel		
2N5089	TO-92	5000 Units/Box		
2N5089G	TO–92 (Pb–Free)	5000 Units/Box		
2N2089RLRA	TO-92	2000/Tape & Reel		
2N2089RLRAG	TO–92 (Pb–Free)	2000/Tape & Reel		
2N2089RLRE	TO-92	2000/Tape & Reel		
2N2089RLREG	TO–92 (Pb–Free)	2000/Tape & Reel		

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## 2N5088, 2N5089

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (Note 2) $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	2N5088 2N5089	V <sub>(BR)CEO</sub>	30 25		Vdc
Collector – Base Breakdown Voltage $(I_C = 100 \ \mu Adc, I_E = 0)$	2N5088 2N5089	V <sub>(BR)CBO</sub>	35 30		Vdc
Collector Cutoff Current $(V_{CB} = 20 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 15 \text{ Vdc}, I_E = 0)$	2N5088 2N5089	I <sub>CBO</sub>		50 50	nAdc
		I <sub>EBO</sub>		50 100	nAdc
ON CHARACTERISTICS			•	-	
DC Current Gain ( $I_C = 100 \ \mu Adc, \ V_{CE} = 5.0 \ Vdc$ )	2N5088 2N5089	h <sub>FE</sub>	300 400	900 1200	-
$(I_{C} = 1.0 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	2N5088 2N5089		350 450		
$(I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$ (Note 2)	2N5088 2N5089		300 400		
Collector – Emitter Saturation Voltage $(I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc})$		V <sub>CE(sat)</sub>	-	0.5	Vdc
Base – Emitter On Voltage ( $I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$ ) (Note 2)		V <sub>BE(on)</sub>	-	0.8	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current–Gain – Bandwidth Product (I <sub>C</sub> = 500 $\mu$ Adc, V <sub>CE</sub> = 5.0 Vdc, f = 20 MHz)		f <sub>T</sub>	50	-	MHz
Collector-Base Capacitance $(V_{CB} = 5.0 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$		C <sub>cb</sub>	-	4.0	pF
Emitter–Base Capacitance ( $V_{EB} = 0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz}$ )		C <sub>eb</sub>	-	10	pF
Small–Signal Current Gain (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 5.0 Vdc, f = 1.0 kHz)	2N5088 2N5089	h <sub>fe</sub>	350 450	1400 1800	_
Noise Figure (I <sub>C</sub> = 100 $\mu$ Adc, V <sub>CE</sub> = 5.0 Vdc, R <sub>S</sub> = 1.0 kΩ, f = 1.0 kHz)	2N5088 2N5089	NF		3.0 2.0	dB

2. Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  2.0%.

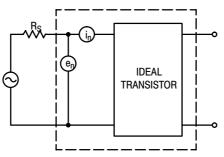


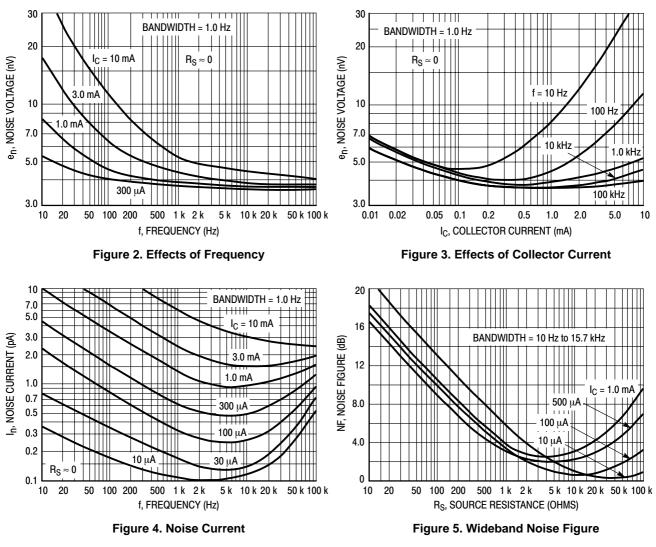
Figure 1. Transistor Noise Model

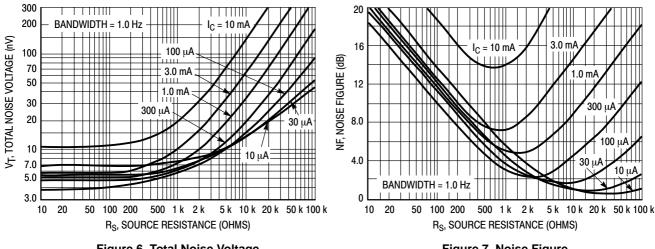
## 2N5088, 2N5089

## **NOISE CHARACTERISTICS**

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$ 

#### NOISE VOLTAGE



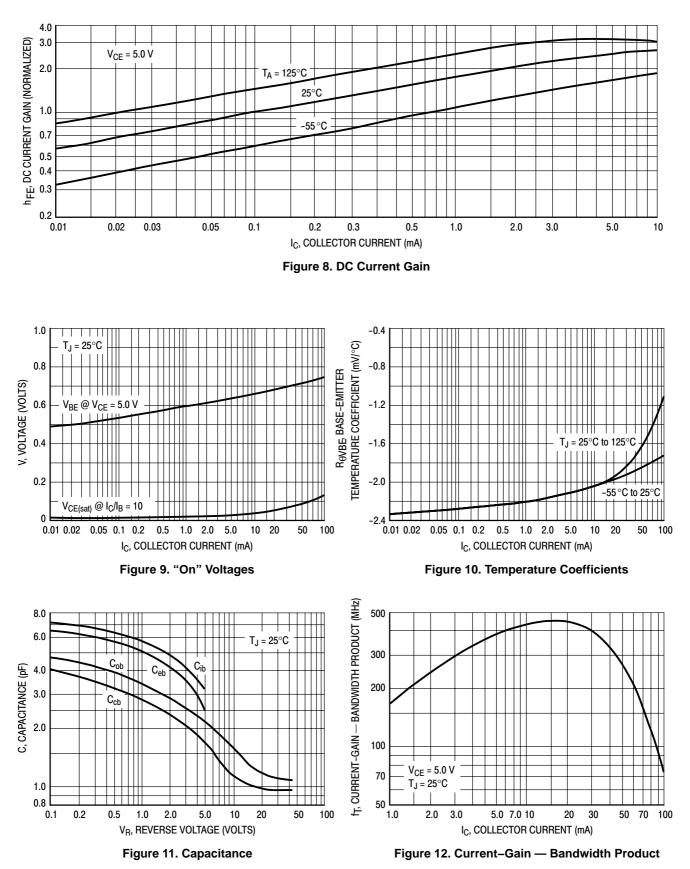


**100 Hz NOISE DATA** 

Figure 6. Total Noise Voltage

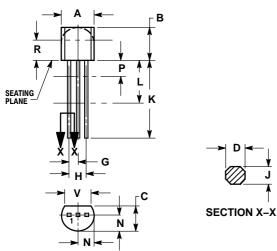
Figure 7. Noise Figure

## 2N5088, 2N5089



#### PACKAGE DIMENSIONS

TO-92 **TO-226AA** CASE 29-11 **ISSUE AL** 





NOTES

- DIMENSIONING AND TOLERANCING PER ANSI 1. Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- 2. 3.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM. 4.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
Κ	0.500		12.70	
L	0.250		6.35	
Ν	0.080	0.105	2.04	2.66
Ρ		0.100		2.54
R	0.115		2.93	
۷	0.135		3.43	

STYLE 1: PIN 1. EMITTER BASE 2 COLLECTOR 3.

ON Semiconductor and 💷 are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC products are not designed, intended, or authorized for use a components in systems intended for surgical implant into the body, or other applications and actual performance may liability of the second to the second intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 61312, Phoenix, Arizona 85082-1312 USA Phone: 480-829-7710 or 800-344-3860 Toll Free USA/Canada Fax: 480-829-7709 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center 2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051 Phone: 81-3-5773-3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.